VUTA010R600NA

Datasheet

60mΩ, 100V, N-Channel Power MOSFET VUTA010R600NA

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
100V	60mΩ@10V	25A

Symbol

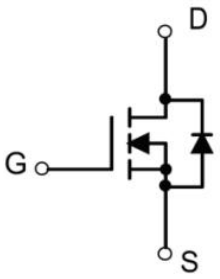


Figure 1 Symbol of VUTA010R600NA

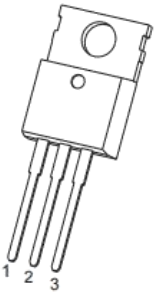
Features

- Excellent package for good heat dissipation
- Low reverse transfer capacitance
- Fast switching capability

Application

- Power switching application

Package Type



TO-220-3L-C

Figure 2 Package Type of VUTA010R600NA

Ordering Information

Product Name	Package
VUTA010R600NA	TO-220-3L-C

Absolute Maximum Ratings (T_C= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current[Note1]	I_D	25	A
Pulsed Drain Current [Note2]	I_{DM}	75	
Single Pulsed Avalanche Energy[Note5]	E_{AS}	256	mJ
Total Power Dissipation[Note4]	P_D	50	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		2.5		ºC/W

Electrical Characteristics (T_C= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 80V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	2.0	3.0	V
Static Drain-Source On-Resistance[Note3]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 8A		46	60	mΩ
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=30V		1680		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		61		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		54		pF
Total Gate Charge	Q_g	V_{DS}=30V		27		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		4		
Gate-Drain Charge	Q_{gd}	I_D= 3A		5		
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 30V		13		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		8		
Turn-off Delay Time	$t_{d(off)}$	I_D= 2A		25		
Turn-off Fall Time	t_f	R_G=2.5Ω, R_L=15Ω		11		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 8A		0.85	1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

5.V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=7A,Starting T_J=25°C

Typical Performance Characteristics

Figure 3: Transfer Characteristics

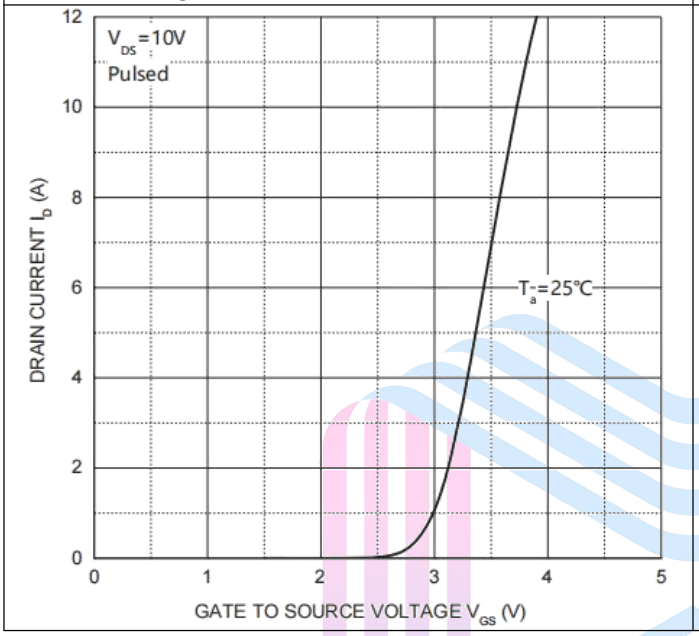


Figure 4: Output Characteristics

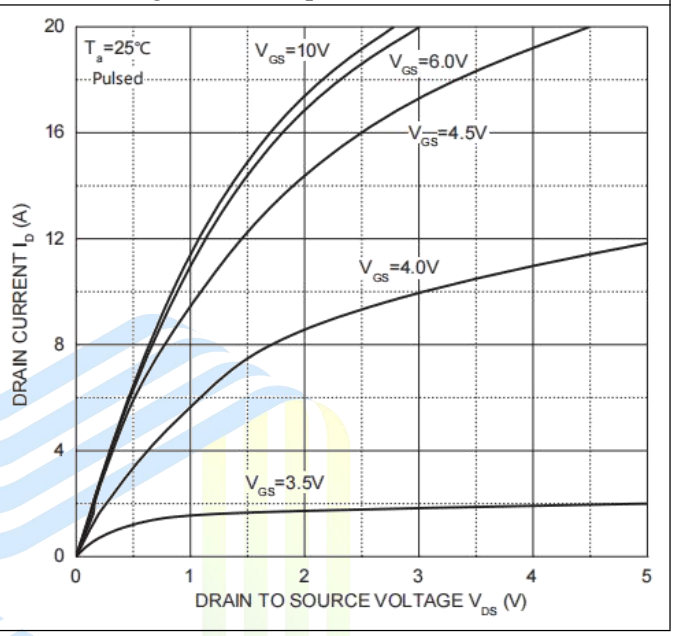


Figure 5: On-Resistance vs. Drain Current

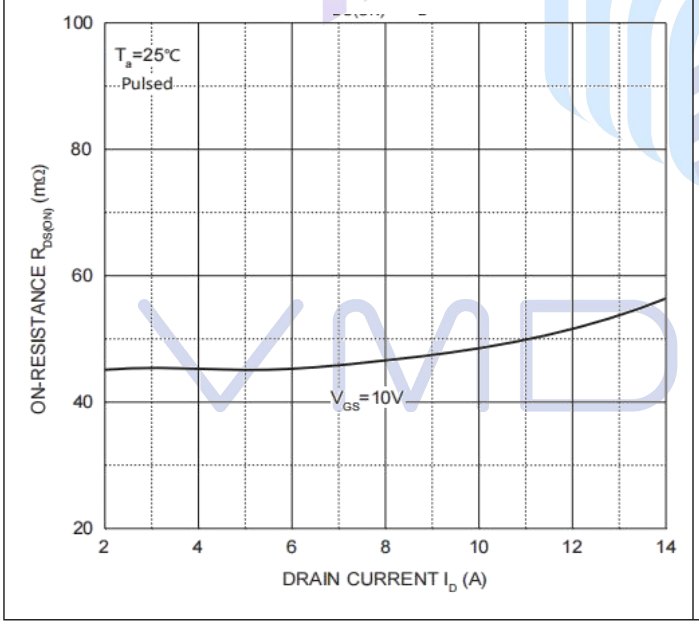


Figure 6: On-Resistance vs. Gate Voltage

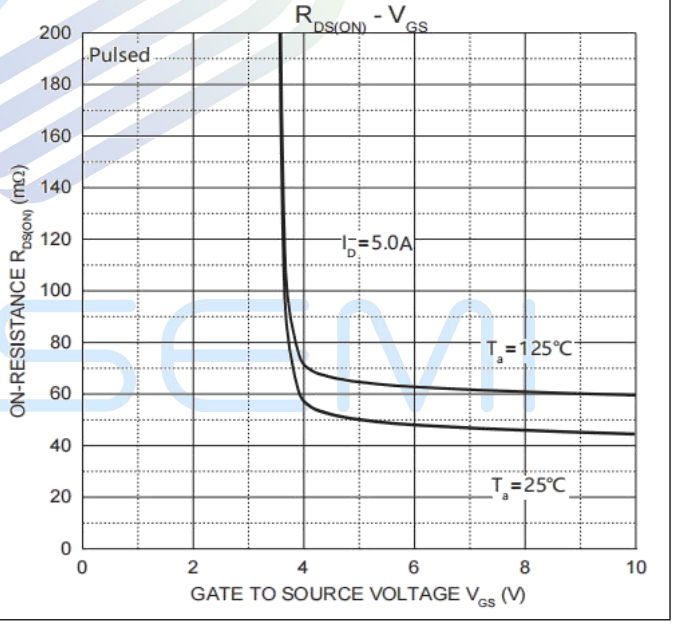


Figure 7: Body Diode Characteristics

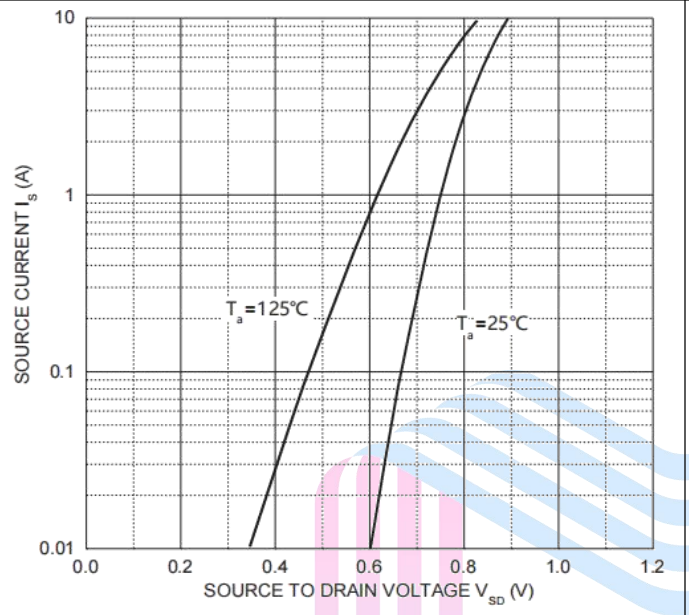
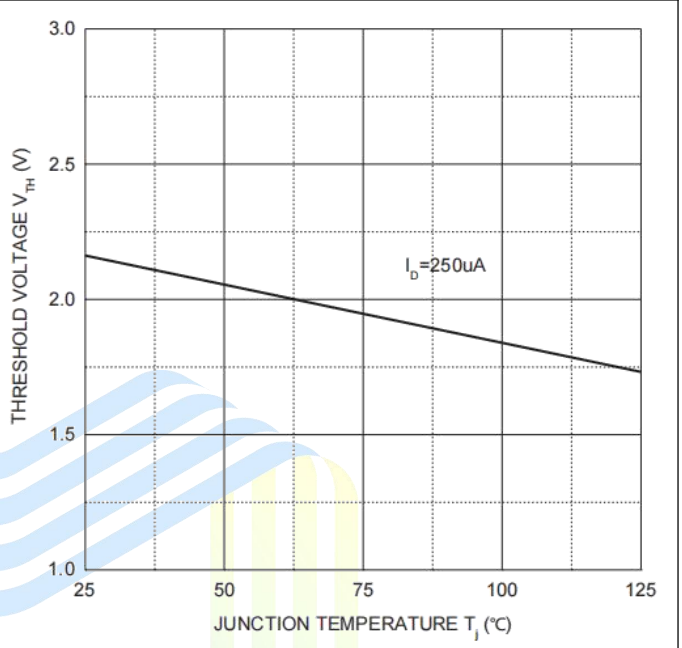
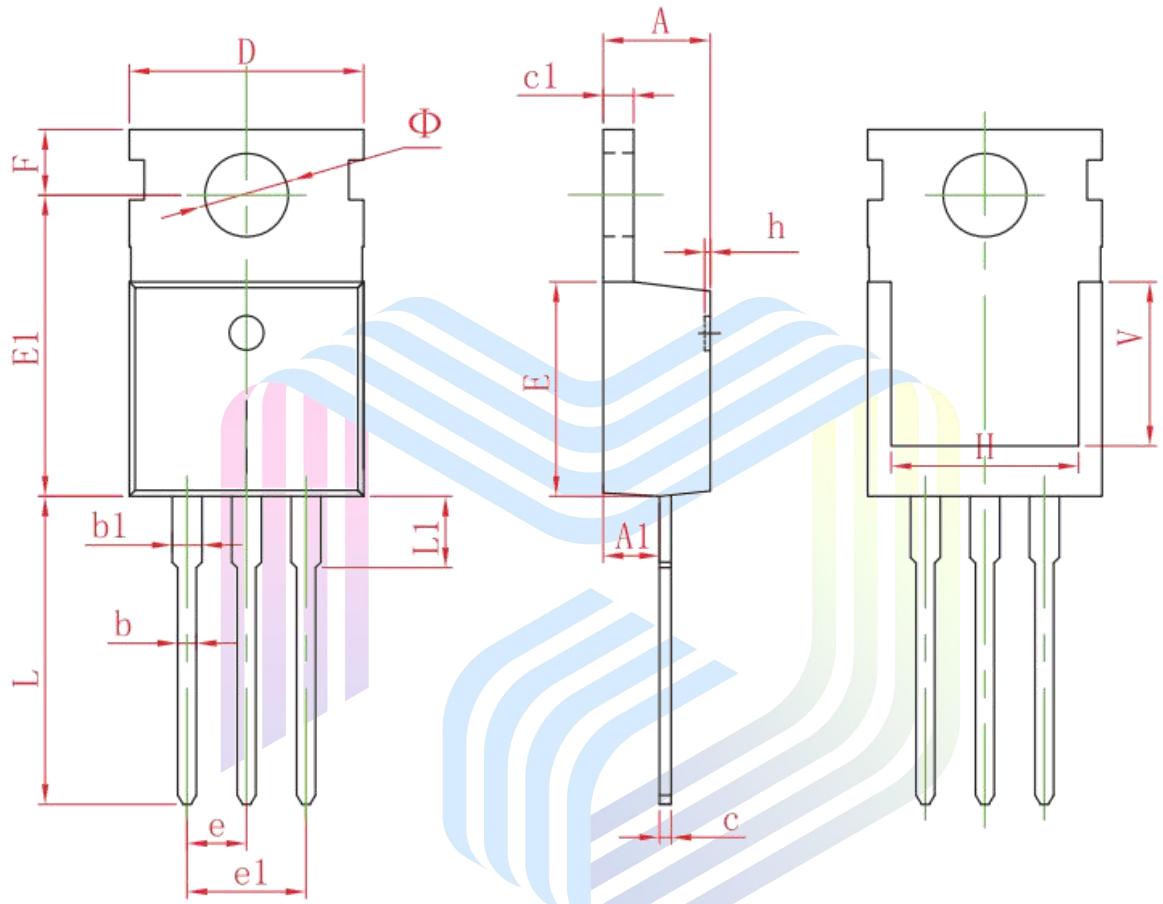


Figure 8: Threshold Voltage



Mechanical Dimensions:

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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